Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-027-9696

Inclosure Material:
Plastic
Overall Length:
0.102 inches
Overall Diameter:
0.060 inches
Function For Which Designed:
Phototransistor
Mounting Method:
Press fit
Semiconductor Material:
Gallium arsenide
Voltage Rating In Volts Per Characteristic:
15.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter to collector, base open
Current Rating Per Characteristic:
7.00 milliamperes operating voltage absolute and 21.00 milliamperes zero-gate-voltage source current absolute
Maximum Operating Tempurature Per Measurement Point:
70.0 degrees celsius ambient air
Terminal Type And Quantity:
2 tab, solder lug and 1 case
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0